Title (en)

PROCESS FOR OBTAINING THIN-FILM CIRCUITS AND PASSIVE CIRCUIT MADE BY SAID PROCESS

Publication

EP 0256568 B1 19910911 (EN)

Application

EP 87201179 A 19870619

Priority

IT 2112686 A 19860715

Abstract (en)

[origin: EP0256568A2] On a single insulating substrate (1) there are deposited in succession a thin layer of tantalium (2) with high resistivity doped with nitrogen and oxygen, a less thin layer of titanium (3) with low resistivity doped with nitrogen, a layer of palladium (4) and a thick layer of gold (7). Selective chemical attacks of said layers then permit tracing of conducting lines (7), resistive lines with greater resistance (10) and resistive lines with less resistance (13).

IPC 1-7

H01L 21/70

IPC 8 full level

H01C 7/18 (2006.01); **H01L 27/01** (2006.01); **H01L 21/3205** (2006.01); **H01L 21/70** (2006.01); **H01L 21/822** (2006.01); **H01L 23/52** (2006.01); **H01L 27/04** (2006.01); **H05K 1/16** (2006.01)

CPC (source: EP US)

H01L 21/707 (2013.01 - EP US); Y10T 29/49082 (2015.01 - EP US); Y10T 29/49099 (2015.01 - EP US)

Cited by

US5152869A; DE10213940A1; FR2837984A1; DE10039710A1; DE10039710B4; EP0333252A3; AU618584B2; WO2006020887A1; US7199016B2; US7884442B2

Designated contracting state (EPC)

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DOCDB simple family (publication)

EP 0256568 A2 19880224; **EP 0256568 A3 19880810**; **EP 0256568 B1 19910911**; DE 3772900 D1 19911017; GR 3003237 T3 19930217; IT 1197776 B 19881206; IT 8621126 A0 19860715; IT 8621126 A1 19880115; JP H07101730 B2 19951101; JP S6329961 A 19880208; NO 173037 B 19930705; NO 173037 C 19931013; NO 872916 D0 19870713; NO 872916 L 19880118; US 5152869 A 19921006

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